

## ZnTe – Zinc Telluride

### DESCRIPTIVE PROPERTIES

<b>Structure formula:</b>	ZnTe
<b>Crystal structure:</b>	cubic
<b>Crystal axis:</b>	(111)
<b>Orientation:</b>	(100); (110); (111) ±30 arc minutes. Other orientations available on request.
<b>Production method:</b>	Markov
<b>Lattice paramters, Å</b>	a = 6.1034
<b>Specific resistivity, Ohm cm</b>	
<b>undoped:</b>	1×10 <sup>6</sup>
<b>doped:</b>	—
<b>Hall mobility, cm<sup>2</sup>/V/sec</b>	130(h)
<b>EPD, cm<sup>-1</sup></b>	< 5×10 <sup>5</sup>
<b>Density of low angle boundaries, cm<sup>-1</sup></b>	< 10
<b>Twins and stacking faults:</b>	twin free
<b>Orientation accuracy:</b>	max. 1°; typ. < 0.5°
<b>Standard wafer sizes:</b>	5 mm x 5 mm, 10 mm x 10 mm and round ø 40 mm
<b>Max. sizes of wafers (at thickness 1 mm):</b>	(111) ø 40 mm (110) 35 x 15 (100) 35 x 15
<b>Standard thickness:</b>	0.5 mm or 1 mm
<b>Tolerances</b>	
<b>Width/Length:</b>	± 0.050 mm
<b>Diameter:</b>	+ 0.000 mm / -0.100 mm
<b>Thickness:</b>	± 0.050 mm
<b>Polishing:</b>	One side or both sides polished Optical Polishing Chemical mechanical polishing

Other sizes and specifications on request.

